

Please replace the paragraph beginning on page 13, line 4, with the following rewritten paragraph:

910 As the material of the first film 11 formed by sputtering or vapor deposition, there may be enumerated, in addition to tungsten, metal such as aluminum, gold, chromium or the like and metal silicide such as molybdenum silicide, tungsten silicide or the like.

Please replace the paragraph beginning on page 14, line 9, with the following rewritten paragraph:

911 Subsequently, a natural oxide formed on the surface of the first films is removed, whereby the surface of the first film is made flat. Thus, the flatness of the surface of an interconnection layer or the contact buried layer is formed of the subsequent second film becomes satisfactory. As a result, the interconnection layer or the contact layer buried layer is formed of the two layer structure comprising the first film and the second film. --

IN THE CLAIMS:

Please cancel claims 7-15 without prejudice or disclaimer, amend claim 1 and add claims 16-20.

912 Sub B1 1. (Amended) In a solid-state imaging device having a light-receiving portion on a semiconductor substrate and a light-shielding film formed so as to cover an electrode formed on said semiconductor substrate on its regions other than a region above

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end

said light-receiving protion, said solid-state imaging device being formed such that said light-shielding film has a mulitlayer structure including first film formed of a film deposited by sputtering or vapor deposition and a second film deposited by chemical vapor deposition.

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16. (newly-added) A solid-state imaging device, comprising:  
a semiconductor substrate;  
a light-receiving portion formed on said substrate; and  
a light-shielding film formed to cover an electrode formed on said semiconductor substrate on its regions other than a region above said light-receiving portion, said light-shielding film comprising a multi-layer structure including a first film formed as an adhesion film and deposited by sputtering or vapor deposition, and a second film deposited by chemical vapor deposition.

17. (newly-added) The solid-state imaging device as set forth in claim 16, wherein said first film is formed of a tungsten film and said second film is formed of a tungsten film.

18. (newly-added) The solid-state imaging device as set forth in claim 16, wherein said electrode is a transfer electrode formed on the semiconductor substrate at its area other than the area in which the light-receiving portion is formed through a gate insulating film, said light-shielding film formed on the transfer electrode through an interlayer insulating film, said light-shielding film preventing light from becoming incident on the transfer electrode.

19. (newly-added) The solid-state imaging device as set forth in claim 18, further comprising an interlayer insulating film formed over the surface of the light-shielding film, a planarization film formed over the surface of the interlayer insulating film, a color filter formed on the planarization film, and a micro-lens formed on the color filter.